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Few recent publications:

1. Vertically aligned Al-doped ZnO nanowire arrays as efficient photoanode for dye sensitized solar cells, S.R. Bhattacharyya, Z. Mullick and R.N. Gayen, J. Electronic. Mater., 49 (2020) 3860-68

2. Fabrication and characterization of transparent nanocrystalline ZnO thin film transistor by a sol-gel technique, S.R. Bhattacharyya and R.N. Gayen, Bul. Mater. Sci. 42 (2019) 167 (1-6)

3. Electrical characteristics and rectification performance of wet chemically synthesized vertically aligned n-ZnO nanowire/p-Si heterojunction, R.N. Gayen and S.R. Bhattacharyya, J. Phys. D: Appl. Phys. 49 (2016) 115102 (1-9)

4. Temperature dependent current transport of Pf/nO nanowire Schottky diodes, R.N. Gayen, S.R. Bhattacharyya and P. Jana, Semicond. Sci. Technol. 20 (2014) 095022 (1-7)

5. Secondary electron emission yield (SEY) in amorphous and graphitic carbon films prepared by PLD, M. Alberti, R. Ayouchi, S.R. Bhattacharyya, N. Bundaleski, A. Moutinho, O. Theodoro, L. Aguilera, M. Taborelli and R. Schwarz, Phys. Status Solidi C 1-3 (2012) /DOI 10.1002/pssc.201100813